

Title (en)

METHOD FOR PRODUCING A MICROSTRUCTURED SURFACE RELIEF BY EMBOSSING THIXOTROPIC LAYERS AND MICROSTRUCTURED SURFACE RELIEF

Title (de)

VERFAHREN ZUR HERSTELLUNG EINES MIKROSTRUKTURIERTEN OBERFLÄCHENRELIEFS DURCH PRÄGEN THIXOTROPER SCHICHTEN UND MIKROSTRUKTURIERTES OBERFLÄCHENRELIEF

Title (fr)

PROCEDE DE PRODUCTION D'UN RELIEF SUPERFICIEL MICROSTRUCTURE PAR ESTAMPAGE DE COUCHES THIXOTROPES ET RELIEF SUPERFICIEL MICROSTRUCTURE

Publication

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Application

**EP 01911478 A 20010112**

Priority

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- EP 0100333 W 20010112

Abstract (en)

[origin: WO0151220A2] The invention relates to a method for producing a microstructured surface relief by applying a coating composition to a substrate. Said coating composition is thixotropic or acquires thixotropic properties on the substrate when pretreated. According to the invention, an embossing device is used to emboss the surface relief into the applied thixotropic coating composition, and the coating composition hardens after removing the embossing device. The substrates which are obtained by using this method and which are provided with a microstructured surface relief are particularly suited for optical, electronic, micromechanical and/or antisoiling applications.

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IPC 8 full level

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